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PIC18F2XK20/4XK20

Flash Memory Programming Specification

1.0 DEVICE OVERVIEW

This document includes the programming specifications for the following devices:

- PIC18F23K20
- PIC18F24K20
- PIC18F25K20
- PIC18F26K20
- PIC18F43K20
- PIC18F44K20
- PIC18F45K20
- PIC18F46K20

2.0 PROGRAMMING OVERVIEW

The PIC18F2XK20/4XK20 devices can be programmed using either the high-voltage In-Circuit Serial Programming™ (ICSP™) method or the low-voltage ICSP method. Both methods can be done with the device in the users' system. The low-voltage ICSP method is slightly different than the high-voltage method and these differences are noted where applicable. This programming specification applies to the PIC18F2XK20/4XK20 devices in all package types.

2.1 Hardware Requirements

In High-Voltage ICSP mode, the PIC18F2XK20/4XK20 devices require two programmable power supplies: one for VDD and one for MCLR/VPP/RE3. Both supplies should have a minimum resolution of 0.25V. Refer to **Section 6.0 “AC/DC Characteristics Timing Requirements for Program/Verify Test Mode”** for additional hardware parameters.

2.1.1 LOW-VOLTAGE ICSP PROGRAMMING

In Low-Voltage ICSP mode, the PIC18F2XK20/4XK20 devices can be programmed using a single VDD source in the operating range. The MCLR/VPP/RE3 does not have to be brought to a different voltage, but can instead be left at the normal operating voltage. Refer to **Section 6.0 “AC/DC Characteristics Timing Requirements for Program/Verify Test Mode”** for additional hardware parameters.

2.2 Pin Diagrams

The pin diagrams for the PIC18F2XK20/4XK20 family are shown in Figure 2-3 and Figure 2-4.

TABLE 2-1: PIN DESCRIPTIONS (DURING PROGRAMMING): PIC18F2XK20/4XK20

Pin Name	During Programming		
	Pin Name	Pin Type	Pin Description
MCLR/VPP/RE3	VPP	P	Programming Enable
VDD ⁽²⁾	VDD	P	Power Supply
VSS ⁽²⁾	VSS	P	Ground
RB5	PGM	I	Low-Voltage ICSP™ input when LVP Configuration bit equals '1' ⁽¹⁾
RB6	PGC	I	Serial Clock
RB7	PGD	I/O	Serial Data

Legend: I = Input, O = Output, P = Power

Note 1: See Figure 5-1 for more information.

2: All power supply (VDD) and ground (VSS) pins must be connected.

PIC18F2XK20/4XK20

FIGURE 2-1: 28-PIN SDIP, SSOP AND SOIC PIN DIAGRAMS

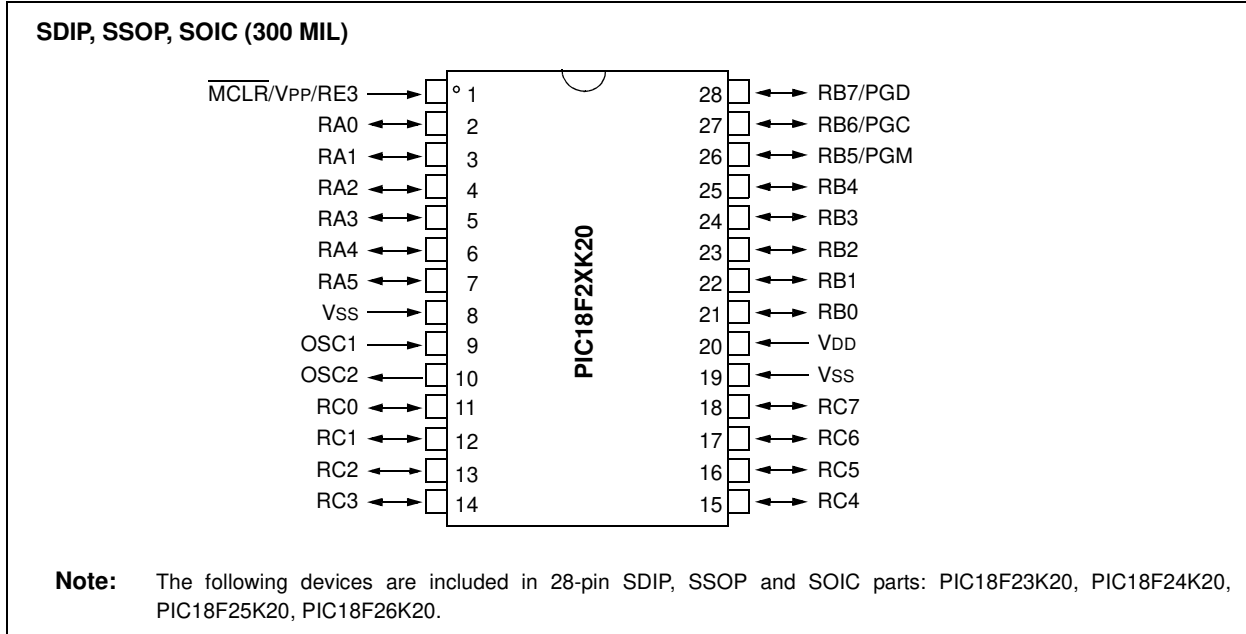
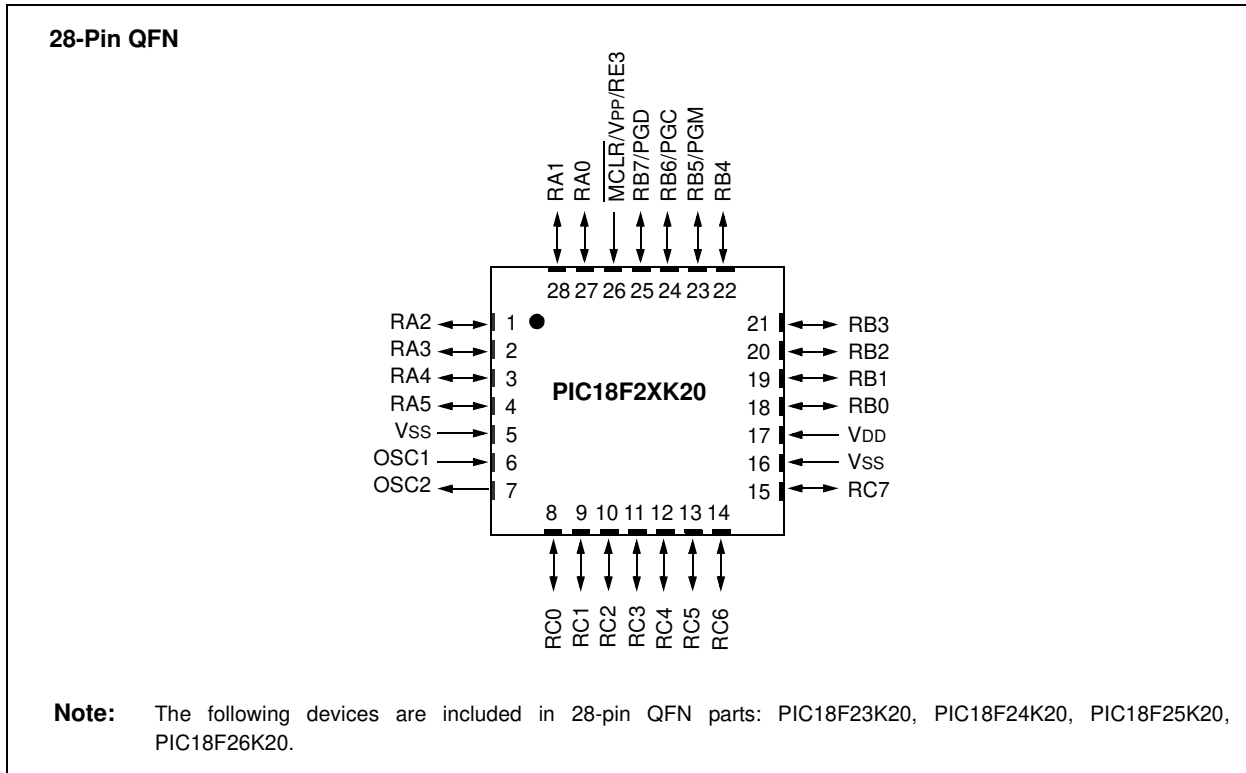


FIGURE 2-2: 28-PIN QFN PIN DIAGRAMS



PIC18F2XK20/4XK20

FIGURE 2-3: 40-PIN PDIP PIN DIAGRAMS

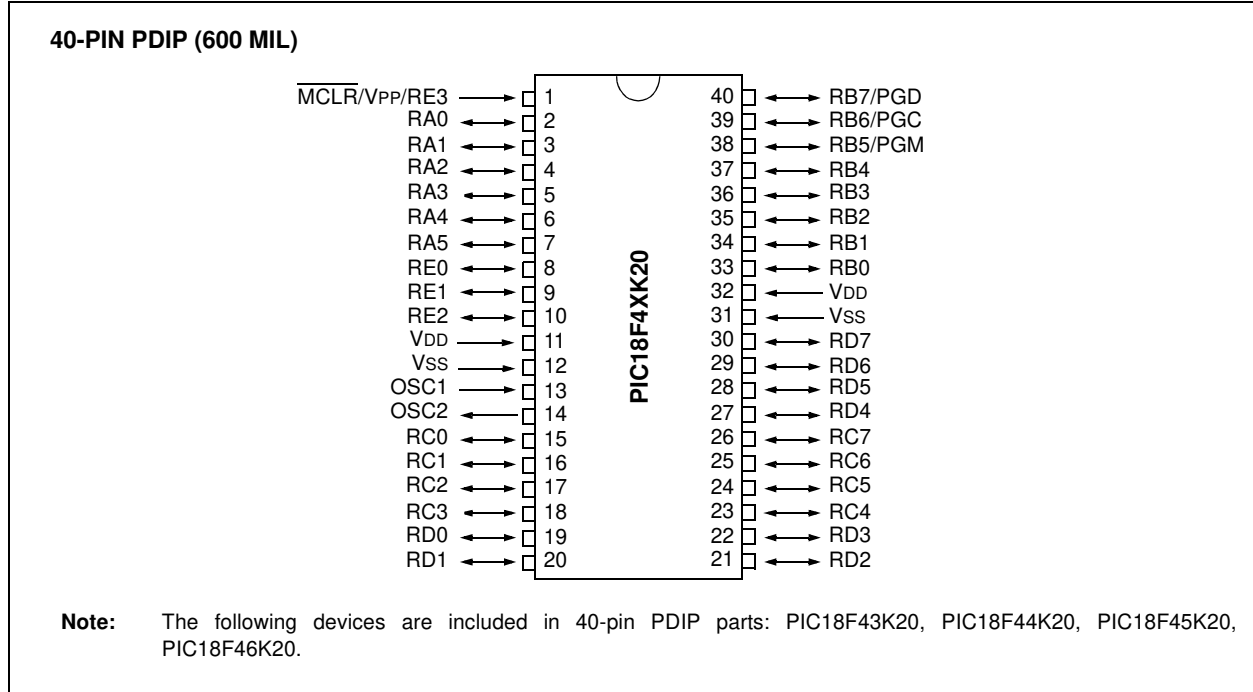
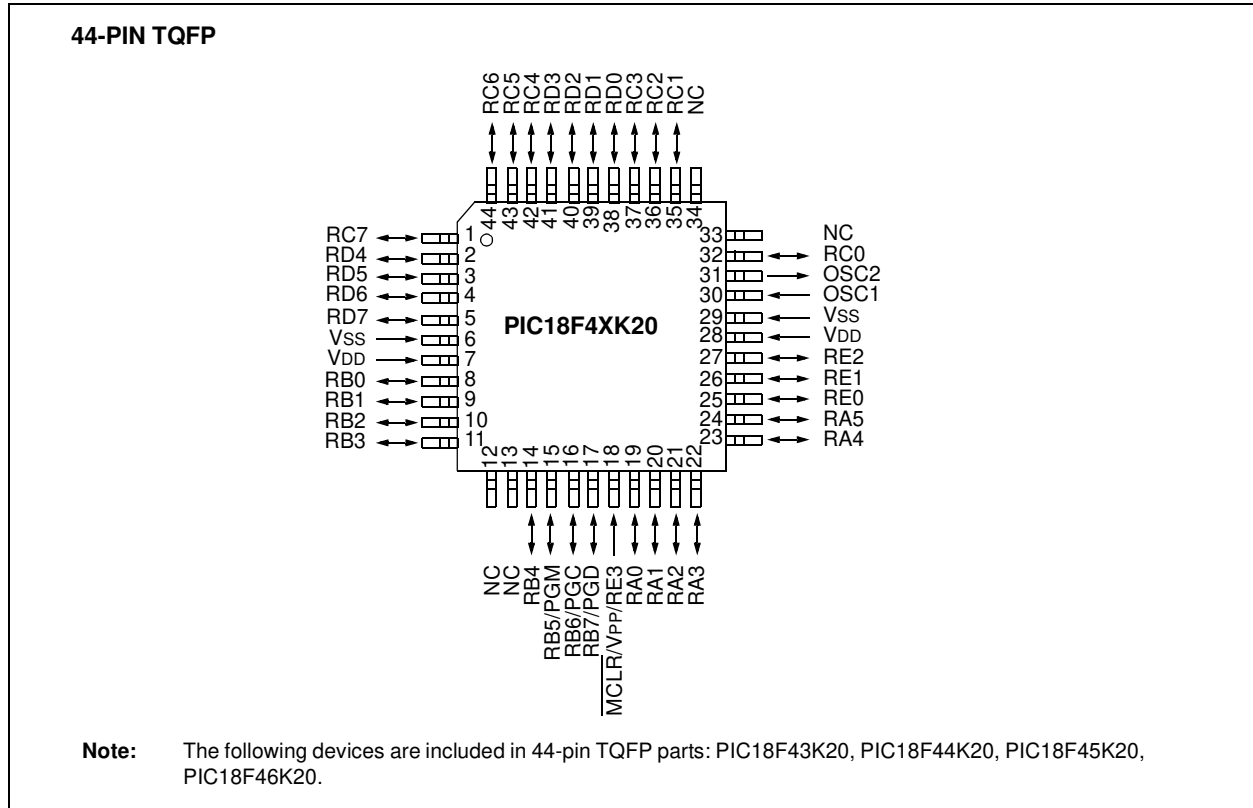
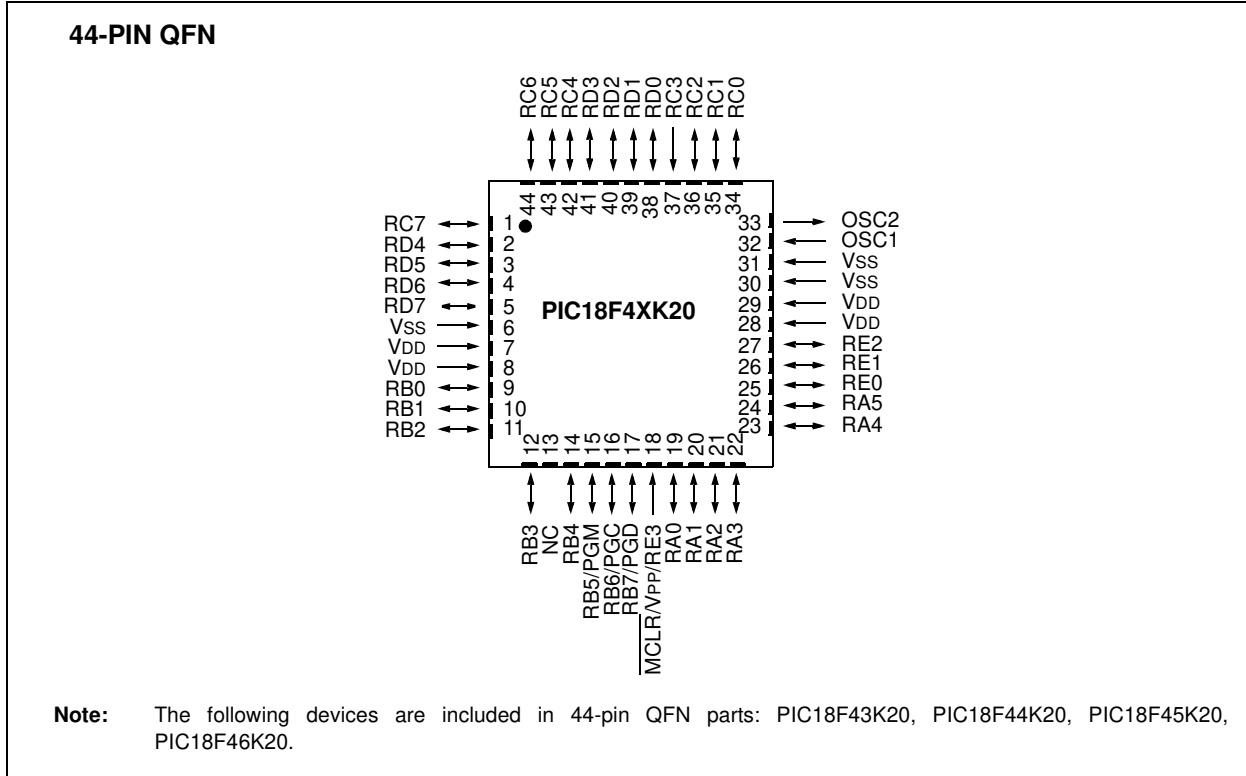


FIGURE 2-4: 44-PIN TQFP PIN DIAGRAMS



PIC18F2XK20/4XK20

FIGURE 2-5: 44-PIN QFN PIN DIAGRAMS



PIC18F2XK20/4XK20

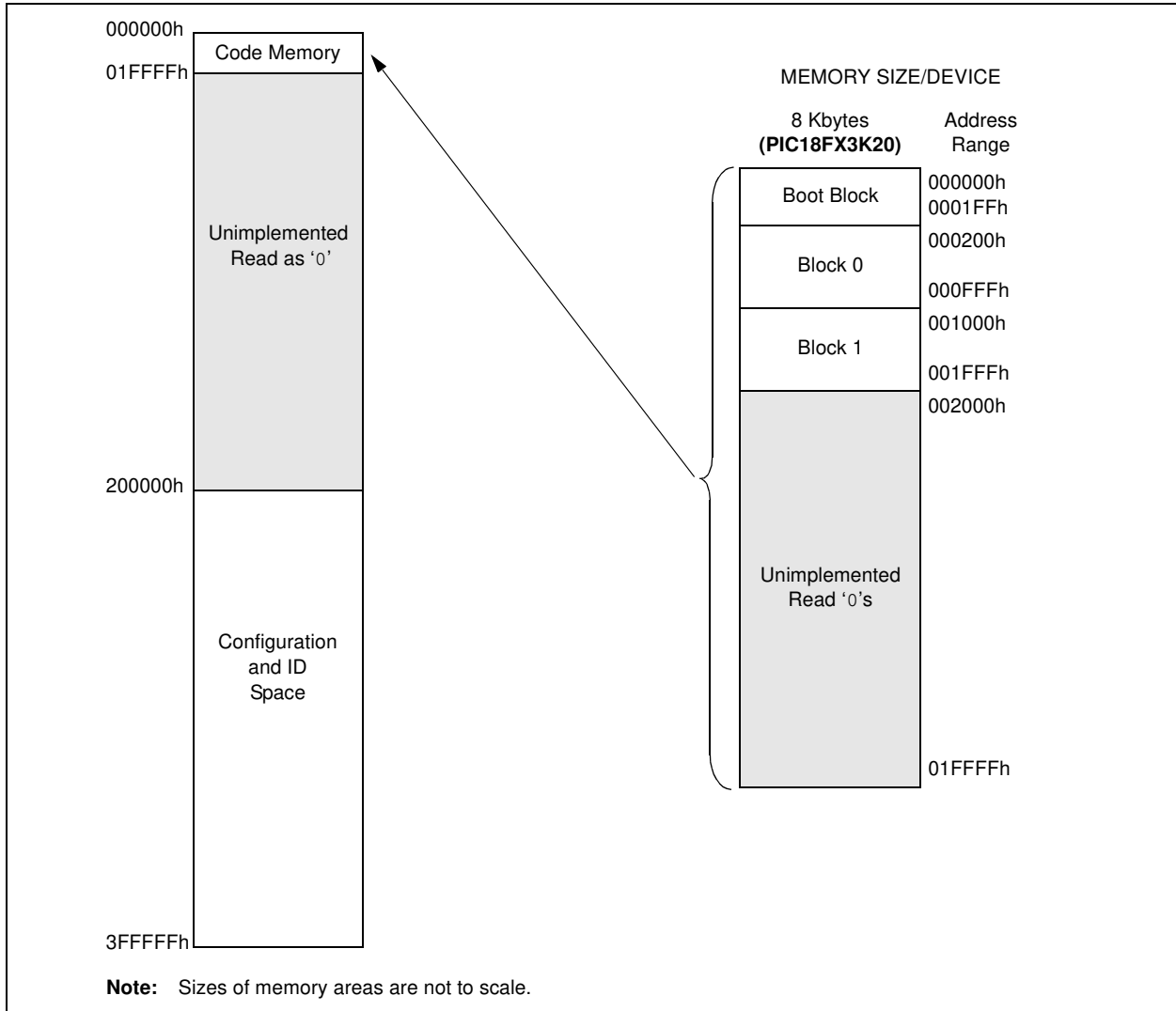
2.3 Memory Maps

For the PIC18FX3K20 devices, the code memory space extends from 00000h to 01FFFh (8 Kbytes) in two 4-Kbyte blocks. Addresses 0000h through 01FFh, however, define a “Boot Block” region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

TABLE 2-2: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F23K20	000000h-001FFFh (8K)
PIC18F43K20	

FIGURE 2-6: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX3K20 DEVICES



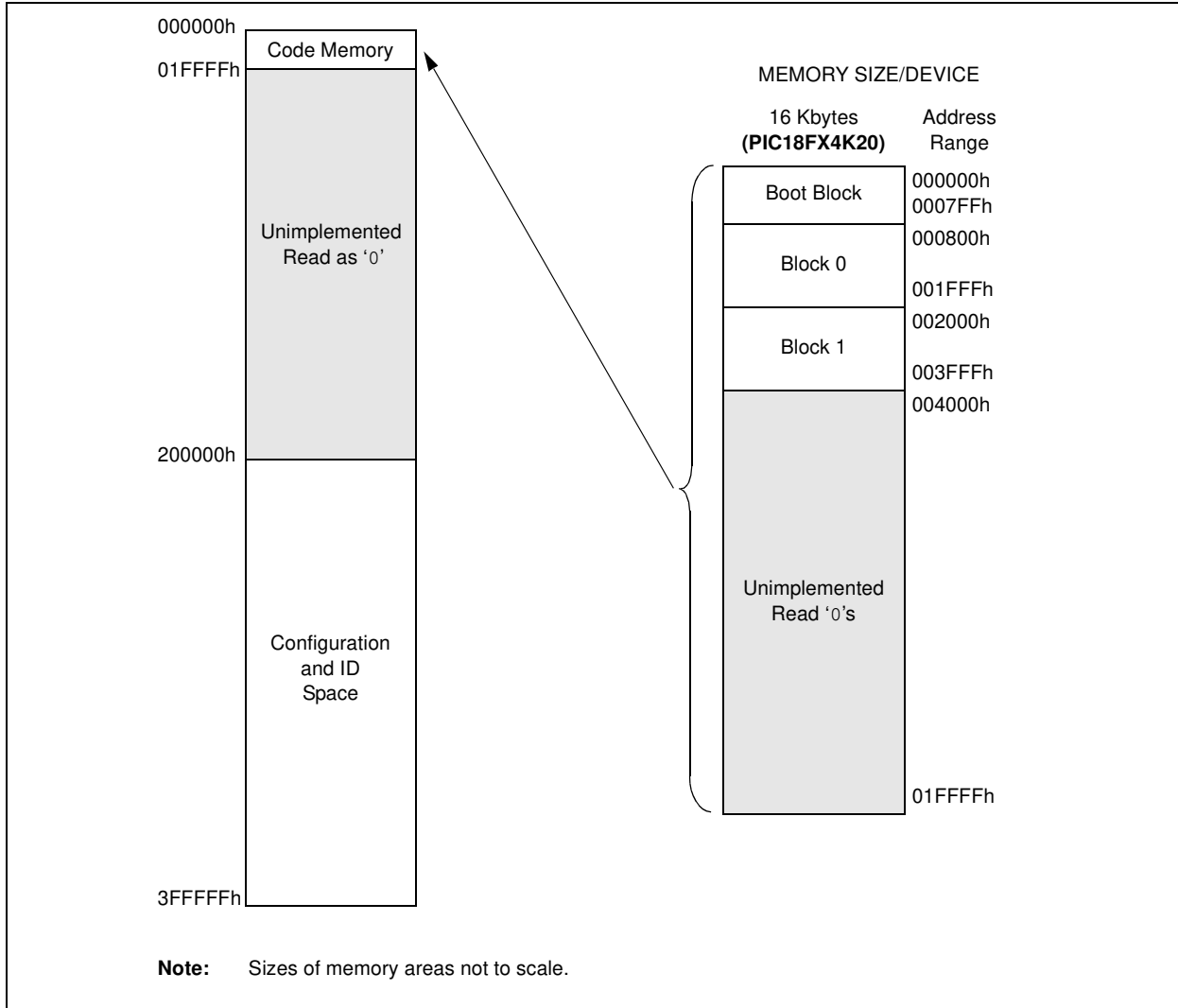
PIC18F2XK20/4XK20

For PIC18FX4K20 devices, the code memory space extends from 000000h to 003FFFh (16 Kbytes) in two 8-Kbyte blocks. Addresses 000000h through 0007FFh, however, define a “Boot Block” region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

TABLE 2-3: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F24K20	000000h-003FFFh (16K)
PIC18F44K20	

FIGURE 2-7: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX4K20 DEVICES



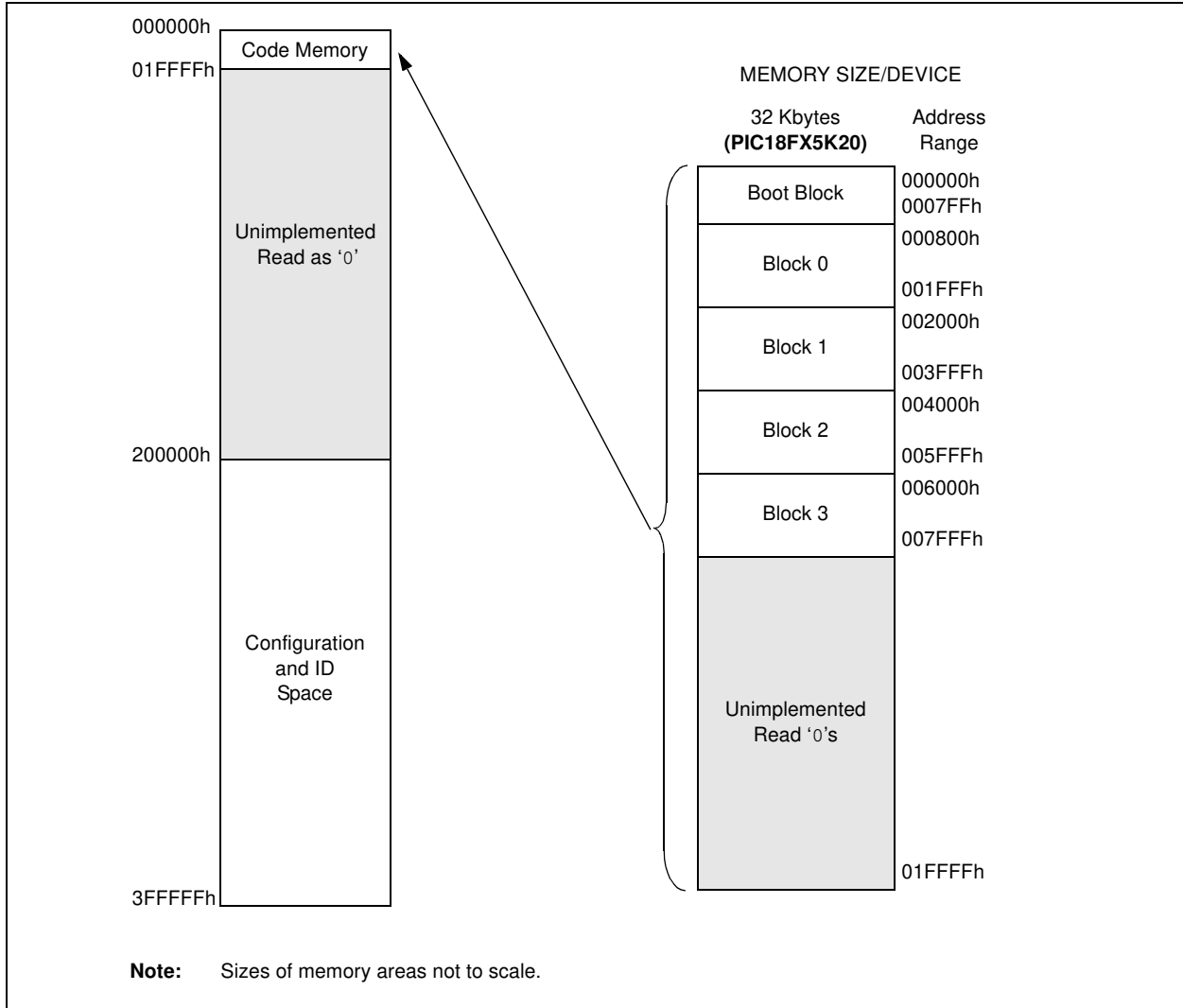
PIC18F2XK20/4XK20

For PIC18FX5K20 devices, the code memory space extends from 000000h to 007FFFh (32 Kbytes) in four 8-Kbyte blocks. Addresses 000000h through 007FFFh, however, define a “Boot Block” region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

TABLE 2-4: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F25K20	000000h-007FFFh (32K)
PIC18F45K20	

FIGURE 2-8: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX5K20 DEVICES



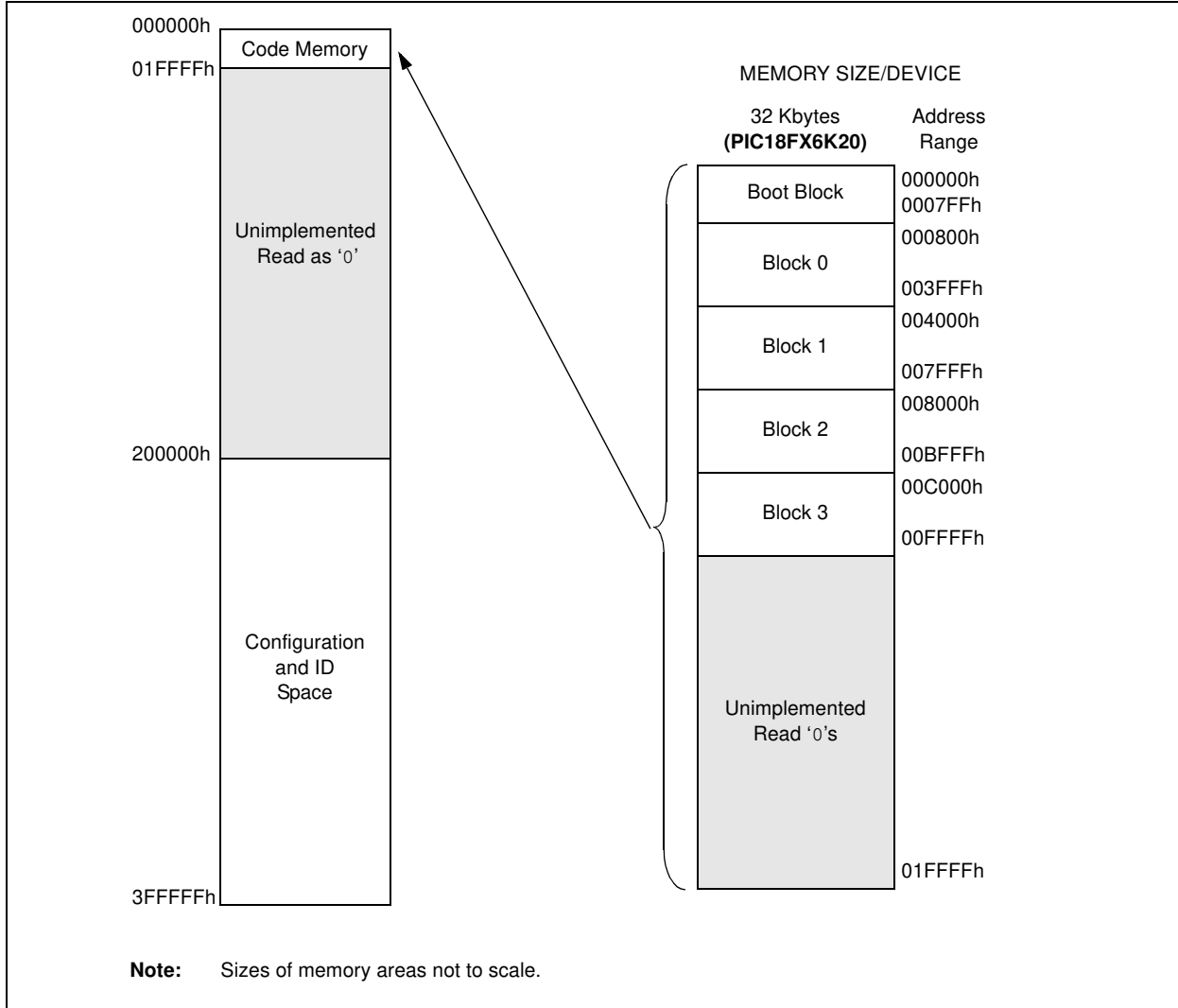
PIC18F2XK20/4XK20

For PIC18FX6K20 devices, the code memory space extends from 000000h to 00FFFFh (64 Kbytes) in four 16-Kbyte blocks. Addresses 000000h through 0007FFh, however, define a “Boot Block” region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

TABLE 2-5: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F26K20	000000h-00FFFFh (64K)
PIC18F46K20	

FIGURE 2-9: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX6K20 DEVICES



In addition to the code memory space, there are three blocks in the configuration and ID space that are accessible to the user through table reads and table writes. Their locations in the memory map are shown in Figure 2-10.

Users may store identification information (ID) in eight ID registers. These ID registers are mapped in addresses 200000h through 200007h. The ID locations read out normally, even after code protection is applied.

Locations 300000h through 30000Dh are reserved for the Configuration bits. These bits select various device options and are described in **Section 5.0 “Configuration Word”**. These Configuration bits read out normally, even after code protection.

Locations 3FFFEh and 3FFFFh are reserved for the device ID bits. These bits may be used by the programmer to identify what device type is being programmed and are described in **Section 5.0 “Configuration Word”**. These device ID bits read out normally, even after code protection.

2.3.1 MEMORY ADDRESS POINTER

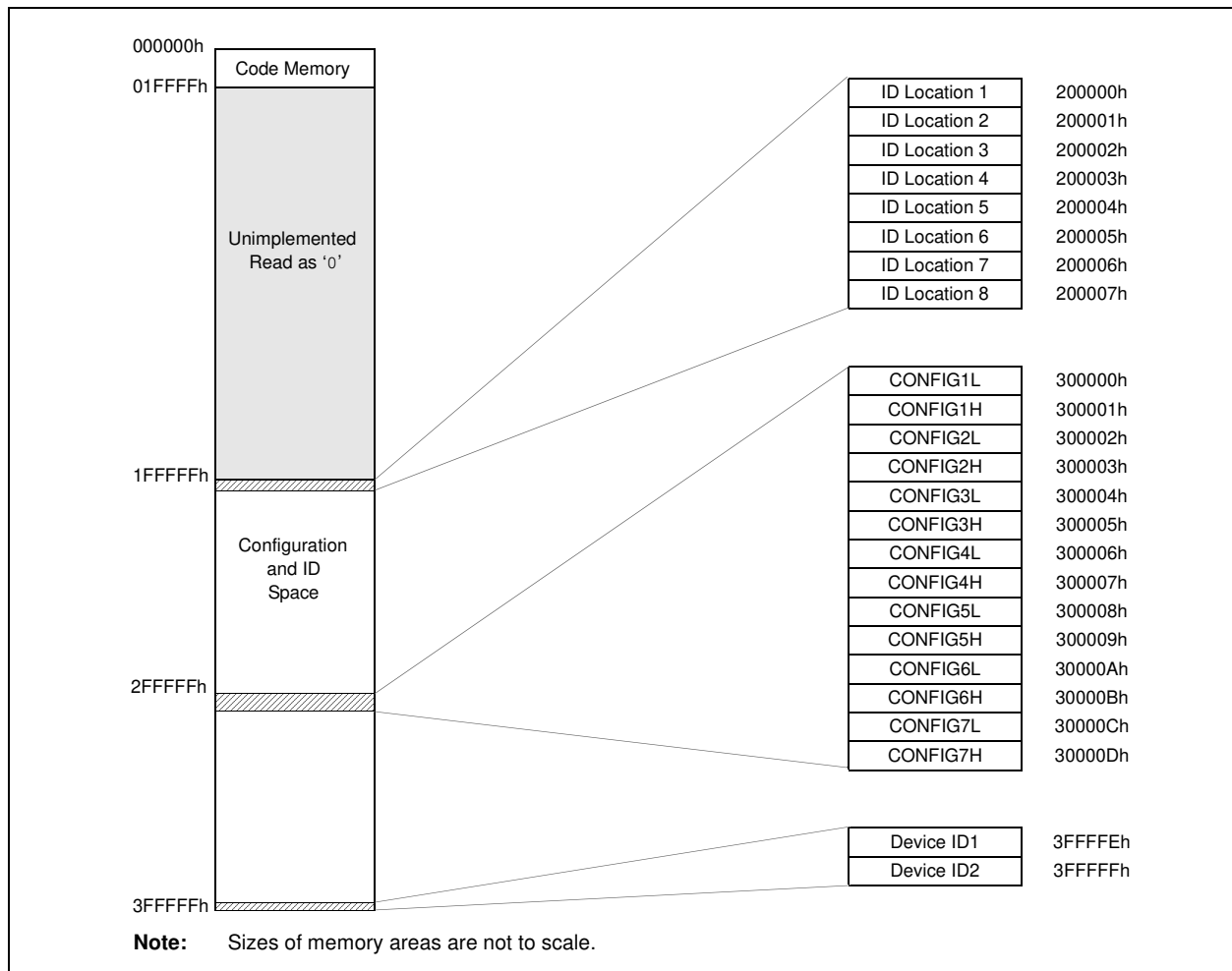
Memory in the address space, 000000h to 3FFFFFFh, is addressed via the Table Pointer register, which is comprised of three Pointer registers:

- TBLPTRU, at RAM address 0FF8h
- TBLPTRH, at RAM address 0FF7h
- TBLPTRL, at RAM address 0FF6h

TBLPTRU	TBLPTRH	TBLPTRL
Addr[21:16]	Addr[15:8]	Addr[7:0]

The 4-bit command, '0000' (core instruction), is used to load the Table Pointer prior to using any read or write operations.

FIGURE 2-10: CONFIGURATION AND ID LOCATIONS FOR PIC18F2XK20/4XK20 DEVICES

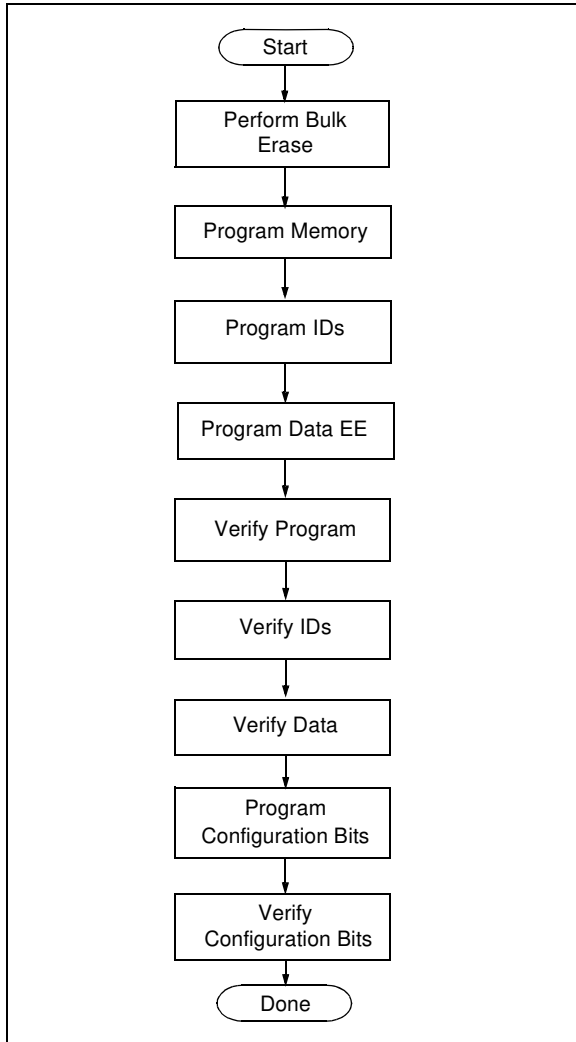


PIC18F2XK20/4XK20

2.4 High-Level Overview of the Programming Process

Figure 2-11 shows the high-level overview of the programming process. First, a Bulk Erase is performed. Next, the code memory, ID locations and data EEPROM are programmed. These memories are then verified to ensure that programming was successful. If no errors are detected, the Configuration bits are then programmed and verified.

FIGURE 2-11: HIGH-LEVEL PROGRAMMING FLOW



2.5 Entering and Exiting High-Voltage ICSP Program/Verify Mode

As shown in Figure 2-12, the High-Voltage ICSP Program/Verify mode is entered by holding PGC and PGD low and then raising $\overline{\text{MCLR}}/\text{VPP}/\text{RE3}$ to $V_{\text{IH}}\text{H}$ (high voltage). Once in this mode, the code memory, data EEPROM, ID locations and Configuration bits can be accessed and programmed in serial fashion. Figure 2-13 shows the exit sequence.

The sequence that enters the device into the Program/Verify mode places all unused I/Os in the high-impedance state.

FIGURE 2-12: ENTERING HIGH-VOLTAGE PROGRAM/VERIFY MODE

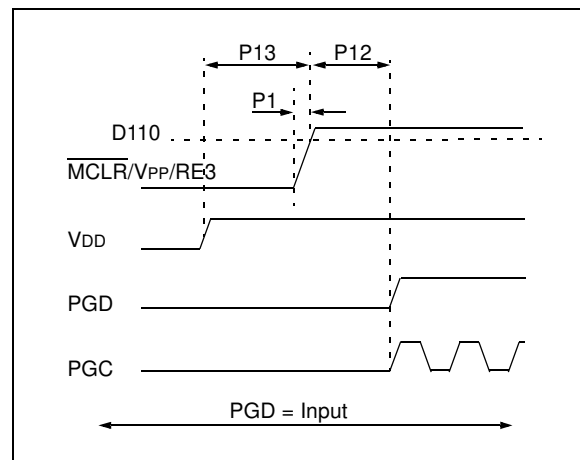
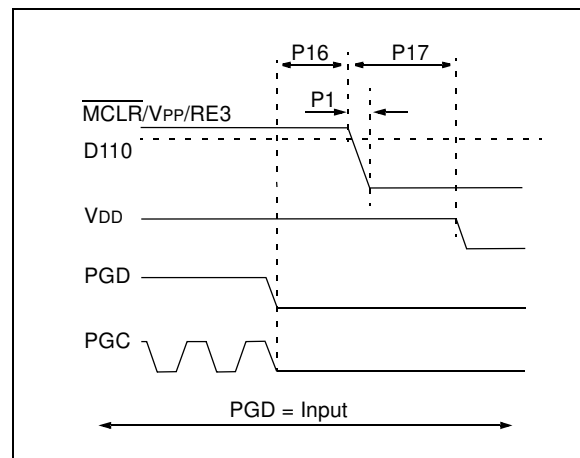


FIGURE 2-13: EXITING HIGH-VOLTAGE PROGRAM/VERIFY MODE



2.6 Entering and Exiting Low-Voltage ICSP Program/Verify Mode

When the LVP Configuration bit is '1' (see **Section 5.3 "Single-Supply ICSP Programming"**), the Low-Voltage ICSP mode is enabled. As shown in Figure 2-14, Low-Voltage ICSP Program/Verify mode is entered by holding PGC and PGD low, placing a logic high on PGM and then raising MCLR/VPP/RE3 to V_{IH} . In this mode, the RB5/PGM pin is dedicated to the programming function and ceases to be a general purpose I/O pin. Figure 2-15 shows the exit sequence.

The sequence that enters the device into the Program/Verify mode places all unused I/Os in the high-impedance state.

FIGURE 2-14: ENTERING LOW-VOLTAGE PROGRAM/VERIFY MODE

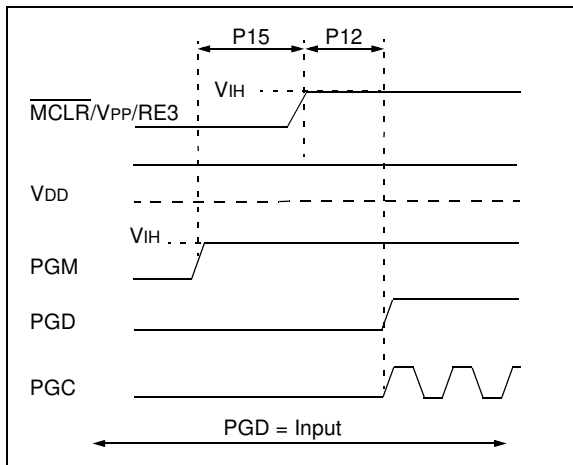
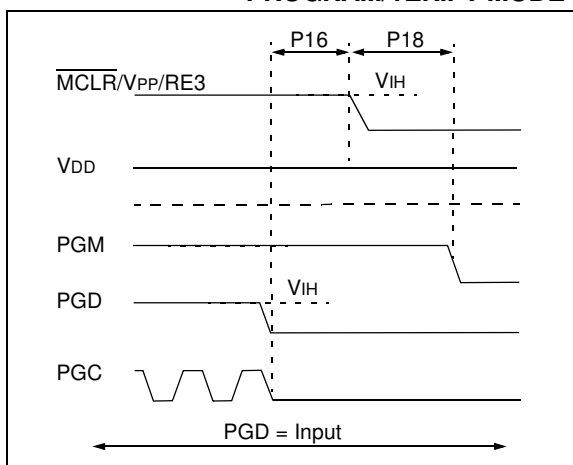


FIGURE 2-15: EXITING LOW-VOLTAGE PROGRAM/VERIFY MODE



2.7 Serial Program/Verify Operation

The PGC pin is used as a clock input pin and the PGD pin is used for entering command bits and data input/output during serial operation. Commands and data are transmitted on the rising edge of PGC, latched on the falling edge of PGC and are Least Significant bit (LSb) first.

2.7.1 4-BIT COMMANDS

All instructions are 20 bits, consisting of a leading 4-bit command followed by a 16-bit operand, which depends on the type of command being executed. To input a command, PGC is cycled four times. The commands needed for programming and verification are shown in Table 2-6.

Depending on the 4-bit command, the 16-bit operand represents 16 bits of input data or 8 bits of input data and 8 bits of output data.

Throughout this specification, commands and data are presented as illustrated in Table 2-7. The 4-bit command is shown Most Significant bit (MSb) first. The command operand, or "Data Payload", is shown <MSB><LSB>. Figure 2-16 demonstrates how to serially present a 20-bit command/operand to the device.

2.7.2 CORE INSTRUCTION

The core instruction passes a 16-bit instruction to the CPU core for execution. This is needed to set up registers as appropriate for use with other commands.

TABLE 2-6: COMMANDS FOR PROGRAMMING

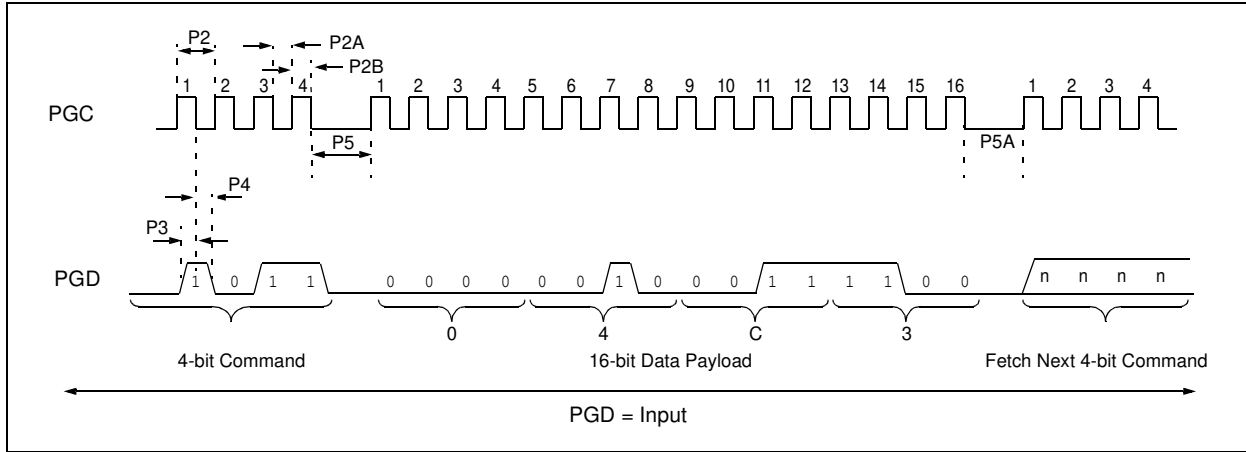
Description	4-Bit Command
Core Instruction (Shift in 16-bit instruction)	0000
Shift out TABLAT register	0010
Table Read	1000
Table Read, post-increment	1001
Table Read, post-decrement	1010
Table Read, pre-increment	1011
Table Write	1100
Table Write, post-increment by 2	1101
Table Write, start programming, post-increment by 2	1110
Table Write, start programming	1111

PIC18F2XK20/4XK20

TABLE 2-7: SAMPLE COMMAND SEQUENCE

4-Bit Command	Data Payload	Core Instruction
1101	3C 40	Table Write, post-increment by 2

FIGURE 2-16: TABLE WRITE, POST-INCREMENT TIMING DIAGRAM (1101)



3.0 DEVICE PROGRAMMING

Programming includes the ability to erase or write the various memory regions within the device.

In all cases, except high-voltage ICSP Bulk Erase, the EECON1 register must be configured in order to operate on a particular memory region.

When using the EECON1 register to act on code memory, the EEPGD bit must be set (EECON1<7> = 1) and the CFGS bit must be cleared (EECON1<6> = 0). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort (e.g., erases) and this must be done prior to initiating a write sequence. The FREE bit must be set (EECON1<4> = 1) in order to erase the program space being pointed to by the Table Pointer. The erase or write sequence is initiated by setting the WR bit (EECON1<1> = 1). It is strongly recommended that the WREN bit only be set immediately prior to a program or erase.

3.1 ICSP Erase

3.1.1 HIGH-VOLTAGE ICSP BULK ERASE

Erasing code or data EEPROM is accomplished by configuring two Bulk Erase Control registers located at 3C0004h and 3C0005h. Code memory may be erased portions at a time, or the user may erase the entire device in one action. Bulk Erase operations will also clear any code-protect settings associated with the memory block erased. Erase options are detailed in Table 3-1. If data EEPROM is code-protected (CPD = 0), the user must request an erase of data EEPROM (e.g., 0084h as shown in Table 3-1).

TABLE 3-1: BULK ERASE OPTIONS

Description	Data (3C0005h:3C0004h)
Chip Erase	0F8Fh
Erase User ID	0088h
Erase Data EEPROM	0084h
Erase Boot Block	0081h
Erase Config Bits	0082h
Erase Code EEPROM Block 0	0180h
Erase Code EEPROM Block 1	0280h
Erase Code EEPROM Block 2	0480h
Erase Code EEPROM Block 3	0880h

The actual Bulk Erase function is a self-timed operation. Once the erase has started (falling edge of the 4th PGC after the NOP command), serial execution will cease until the erase completes (parameter P11). During this time, PGC may continue to toggle but PGD must be held low.

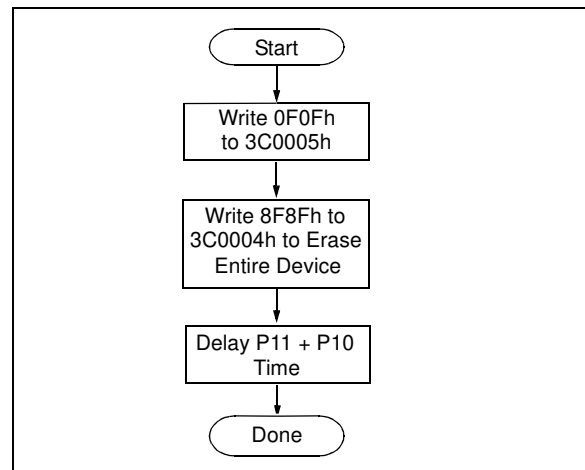
The code sequence to erase the entire device is shown in Table 3-2 and the flowchart is shown in Figure 3-1.

Note: A Bulk Erase is the only way to reprogram code-protect bits from an “on” state to an “off” state.

TABLE 3-2: BULK ERASE COMMAND SEQUENCE

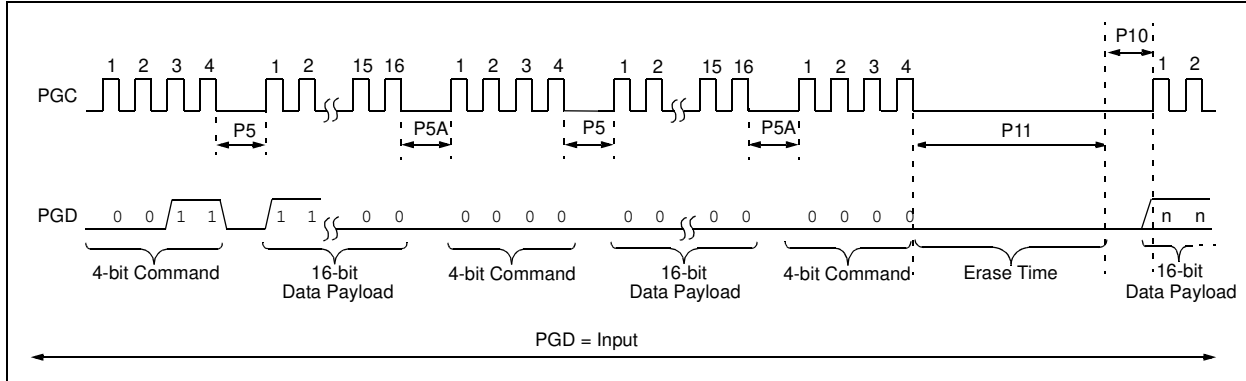
4-Bit Command	Data Payload	Core Instruction
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 05	MOVLW 05h
0000	6E F6	MOVWF TBLPTRL
1100	0F 0F	Write 0Fh to 3C0005h
0000	0E 3C	MOVLW 3Ch
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 04	MOVLW 04h
0000	6E F6	MOVWF TBLPTRL
1100	8F 8F	Write 8F8Fh TO 3C0004h to erase entire device.
0000	00 00	NOP
0000	00 00	Hold PGD low until erase completes.

FIGURE 3-1: BULK ERASE FLOW



PIC18F2XK20/4XK20

FIGURE 3-2: BULK ERASE TIMING DIAGRAM



3.1.2 LOW-VOLTAGE ICSP BULK ERASE

When using low-voltage ICSP, the part must be supplied by the voltage specified in parameter D111 if a Bulk Erase is to be executed. All other Bulk Erase details as described above apply.

If it is determined that a program memory erase must be performed at a supply voltage below the Bulk Erase limit, refer to the erase methodology described in **Section 3.1.3 “ICSP Row Erase”** and **Section 3.2.1 “Modifying Code Memory”**.

If it is determined that a data EEPROM erase must be performed at a supply voltage below the Bulk Erase limit, follow the methodology described in **Section 3.3 “Data EEPROM Programming”** and write ‘1’s to the array.

3.1.3 ICSP ROW ERASE

Regardless of whether high or low-voltage ICSP is used, it is possible to erase one row (64 bytes of data), provided the block is not code or write-protected. Rows are located at static boundaries beginning at program memory address 000000h, extending to the internal program memory limit (see **Section 2.3 “Memory Maps”**).

The Row Erase duration is self-timed. After the WR bit in EECON1 is set, two NOPs are issued. Erase starts upon the 4th PGC of the second NOP. It ends when the WR bit is cleared by hardware.

The code sequence to Row Erase a PIC18F2XK20/4XK20 device is shown in Table 3-3. The flowchart shown in Figure 3-3 depicts the logic necessary to completely erase a PIC18F2XK20/4XK20 device. The timing diagram for Row Erase is identical to the data EEPROM write timing shown in Figure 3-7.

Note: The TBLPTR register can point at any byte within the row intended for erase.

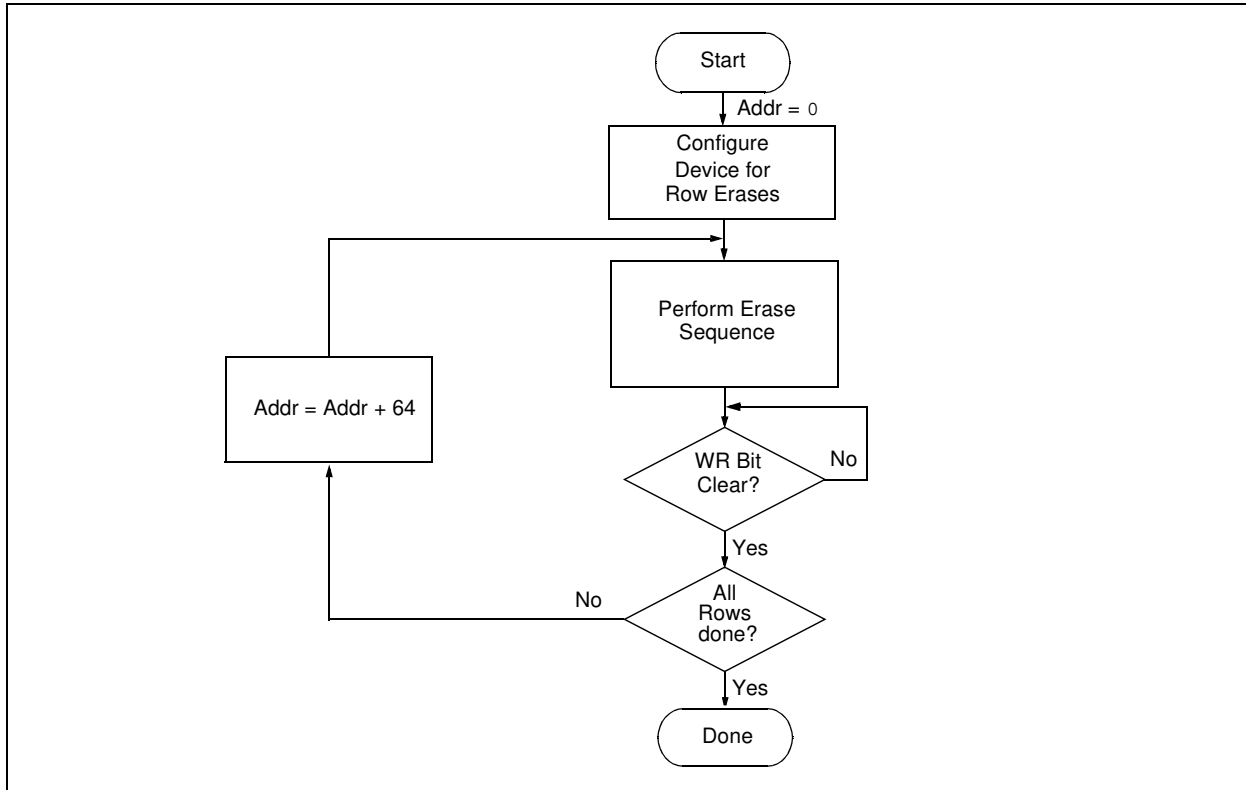
TABLE 3-3: ERASE CODE MEMORY CODE SEQUENCE

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory and enable writes.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2: Point to first row in code memory.		
0000	6A F8	CLRF TBLPTRU
0000	6A F7	CLRF TBLPTRH
0000	6A F6	CLRF TBLPTRL
Step 3: Enable erase and erase single row.		
0000	88 A6	BSF EECON1, FREE
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP
0000	00 00	NOP Erase starts on the 4th clock of this instruction
Step 4: Poll WR bit. Repeat until bit is clear.		
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0010	<MSB><LSB>	Shift out data ⁽¹⁾
Step 5: Hold PGC low for time P10.		
Step 6: Repeat step 3 with Address Pointer incremented by 64 until all rows are erased.		
Step 7: Disable writes.		
0000	94 A6	BCF EECON1, WREN

Note 1: See Figure 4-4 for details on shift out data timing.

PIC18F2XK20/4XK20

FIGURE 3-3: SINGLE ROW ERASE CODE MEMORY FLOW



3.2 Code Memory Programming

Programming code memory is accomplished by first loading data into the write buffer and then initiating a programming sequence. The write and erase buffer sizes shown in Table 3-4 can be mapped to any location of the same size beginning at 000000h. The actual memory write sequence takes the contents of this buffer and programs the proper amount of code memory that contains the Table Pointer.

The programming duration is externally timed and is controlled by PGC. After a Start Programming command is issued (4-bit command, '1111'), a NOP is issued, where the 4th PGC is held high for the duration of the programming time, P9.

After PGC is brought low, the programming sequence is terminated. PGC must be held low for the time specified by parameter P10 to allow high-voltage discharge of the memory array.

The code sequence to program a PIC18F2XK20/4XK20 device is shown in Table 3-5. The flowchart shown in Figure 3-4 depicts the logic necessary to completely write a PIC18F2XK20/4XK20 device. The timing diagram that details the Start Programming command and parameters P9 and P10 is shown in Figure 3-5.

Note: The TBLPTR register must point to the same region when initiating the programming sequence as it did when the write buffers were loaded.

TABLE 3-4: WRITE AND ERASE BUFFER SIZES

Devices (Arranged by Family)	Write Buffer Size (bytes)	Erase Size (bytes)
PIC18F26K20, PIC18F46K20	64	64
PIC18F24K20, PIC18F25K20, PIC18F44K20, PIC18F45K20	32	64
PIC18F23K20, PIC18F43K20	16	64

TABLE 3-5: WRITE CODE MEMORY CODE SEQUENCE

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2: Point to row to write.		
0000	0E <Addr[21:16]>	MOVLW <Addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <Addr[15:8]>	MOVLW <Addr[15:8]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <Addr[7:0]>	MOVLW <Addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
Step 3: Load write buffer. Repeat for all but the last two bytes.		
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
Step 4: Load write buffer for last two bytes and start programming.		
1111	<MSB><LSB>	Write 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
To continue writing data, repeat steps 2 through 4, where the Address Pointer is incremented by 2 at each iteration of the loop.		

PIC18F2XK20/4XK20

FIGURE 3-4: PROGRAM CODE MEMORY FLOW

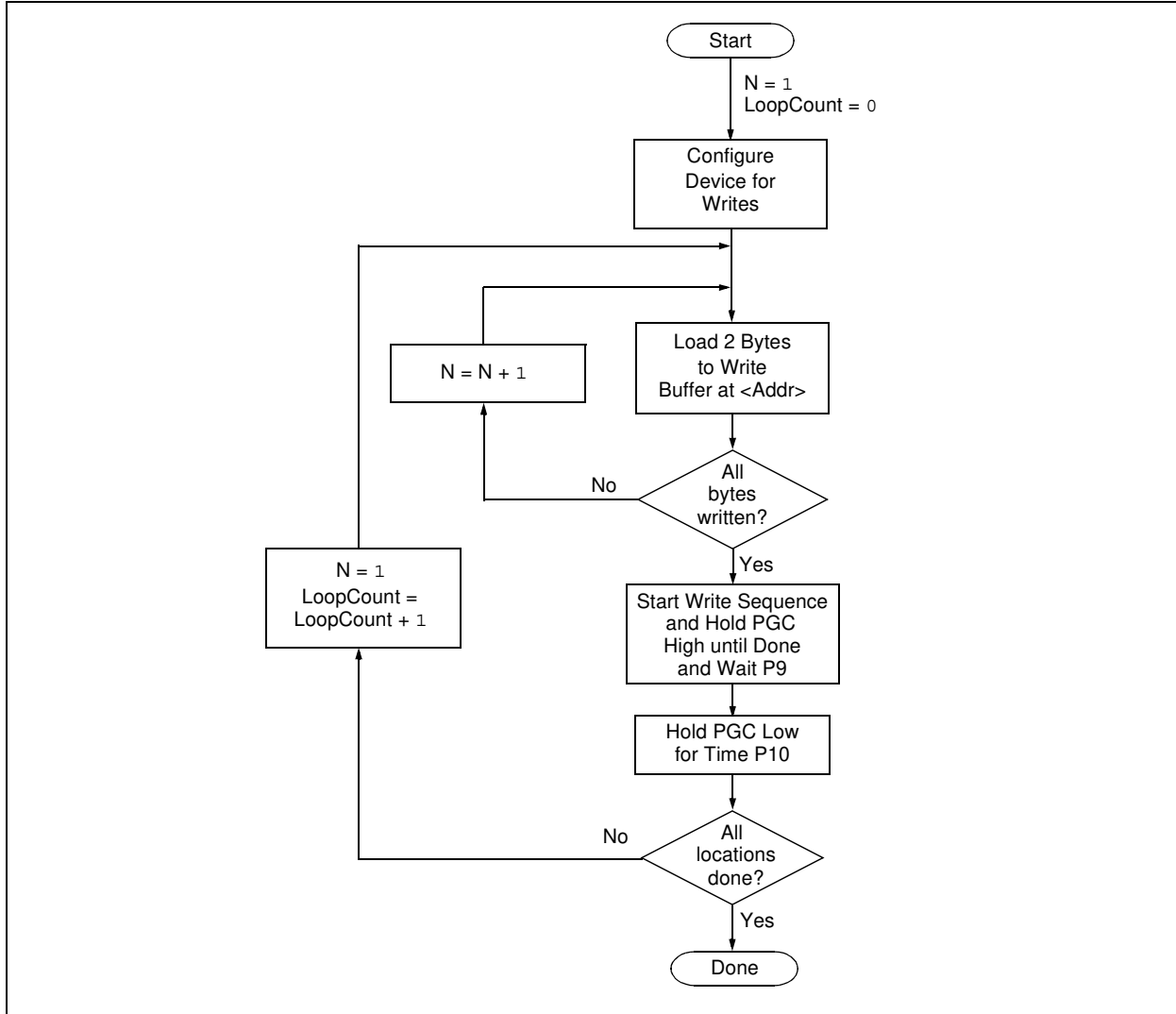
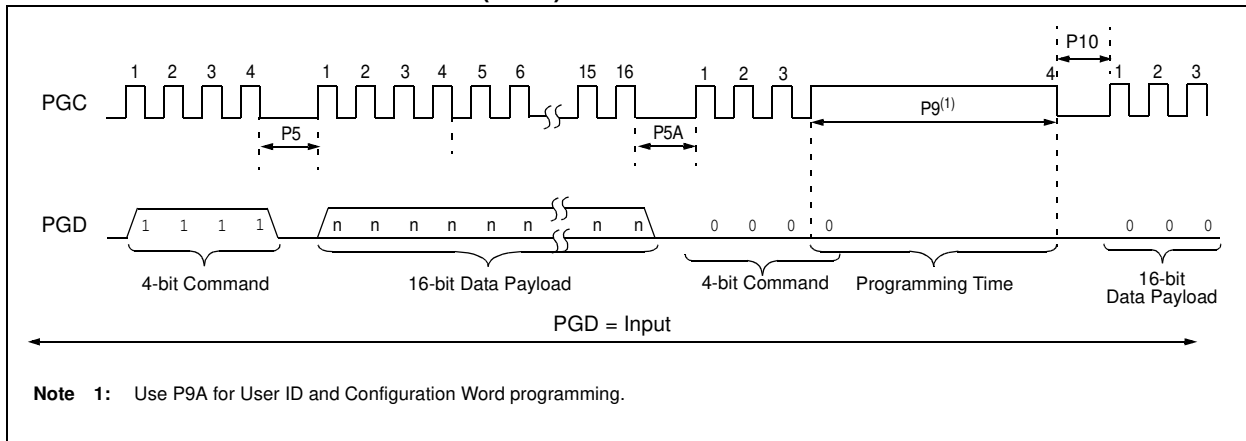


FIGURE 3-5: TABLE WRITE AND START PROGRAMMING INSTRUCTION TIMING DIAGRAM (1111)



3.2.1 MODIFYING CODE MEMORY

The previous programming example assumed that the device has been Bulk Erased prior to programming (see **Section 3.1.1 “High-Voltage ICSP Bulk Erase”**). It may be the case, however, that the user wishes to modify only a section of an already programmed device.

The appropriate number of bytes required for the erase buffer must be read out of code memory (as described in **Section 4.2 “Verify Code Memory and ID Locations”**) and buffered. Modifications can be made on this buffer. Then, the block of code memory that was read out must be erased and rewritten with the modified data.

The WREN bit must be set if the WR bit in EECON1 is used to initiate a write sequence.

TABLE 3-6: MODIFYING CODE MEMORY

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 2: Read code memory into buffer (Section 4.1 “Read Code Memory, ID Locations and Configuration Bits”).		
Step 3: Set the Table Pointer for the block to be erased.		
0000	0E <Addr[21:16]>	MOVLW <Addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <Addr[8:15]>	MOVLW <Addr[8:15]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <Addr[7:0]>	MOVLW <Addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
Step 4: Enable memory writes and setup an erase.		
0000	84 A6	BSF EECON1, WREN
0000	88 A6	BSF EECON1, FREE
Step 5: Initiate erase.		
0000	88 A6	BSF EECON1, FREE
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP
0000	00 00	NOP Erase starts on the 4th clock of this instruction
Step 6: Poll WR bit. Repeat until bit is clear.		
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0000	<MSB><LSB>	Shift out data ⁽¹⁾
Step 7: Load write buffer. The correct bytes will be selected based on the Table Pointer.		
0000	0E <Addr[21:16]>	MOVLW <Addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <Addr[8:15]>	MOVLW <Addr[8:15]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <Addr[7:0]>	MOVLW <Addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
.	.	
.	.	Repeat as many times as necessary to fill the write buffer
.	.	Write 2 bytes and start programming.
1111	<MSB><LSB>	NOP - hold PGC high for time P9 and low for time P10.
0000	00 00	
To continue modifying data, repeat Steps 2 through 6, where the Address Pointer is incremented by the appropriate number of bytes (see Table 3-4) at each iteration of the loop. The write cycle must be repeated enough times to completely rewrite the contents of the erase buffer.		
Step 8: Disable writes.		
0000	94 A6	BCF EECON1, WREN

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3.3 Data EEPROM Programming

Data EEPROM is accessed one byte at a time via an Address Pointer (register pair EEADRH:EEADR) and a data latch (EEDATA). Data EEPROM is written by loading EEADRH:EEADR with the desired memory location, EEDATA with the data to be written and initiating a memory write by appropriately configuring the EECON1 register. A byte write automatically erases the location and writes the new data (erase-before-write).

When using the EECON1 register to perform a data EEPROM write, both the EEPGD and CFGS bits must be cleared ($EECON1\langle 7:6 \rangle = 00$). The WREN bit must be set ($EECON1\langle 2 \rangle = 1$) to enable writes of any sort and this must be done prior to initiating a write sequence. The write sequence is initiated by setting the WR bit ($EECON1\langle 1 \rangle = 1$).

The write begins on the falling edge of the 24th PGC after the WR bit is set. It ends when the WR bit is cleared by hardware.

After the programming sequence terminates, PGC must be held low for the time specified by parameter P10 to allow high-voltage discharge of the memory array.

FIGURE 3-6: PROGRAM DATA FLOW

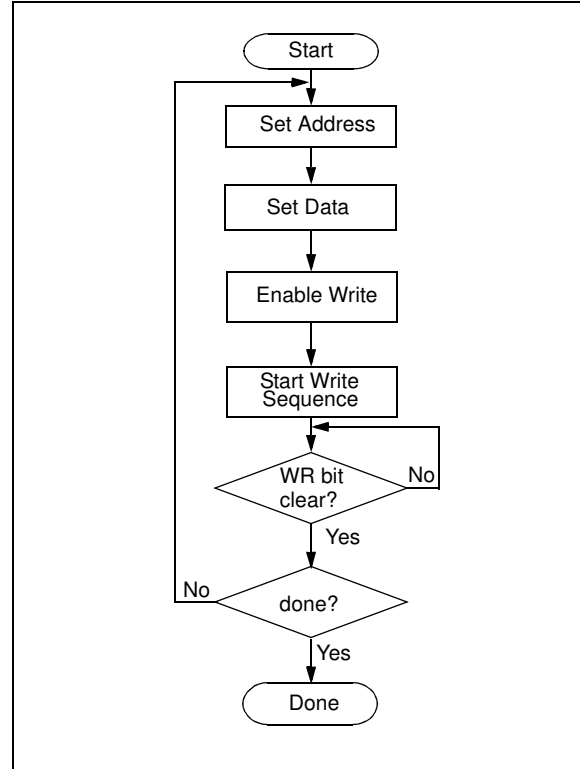


FIGURE 3-7: DATA EEPROM WRITE TIMING DIAGRAM

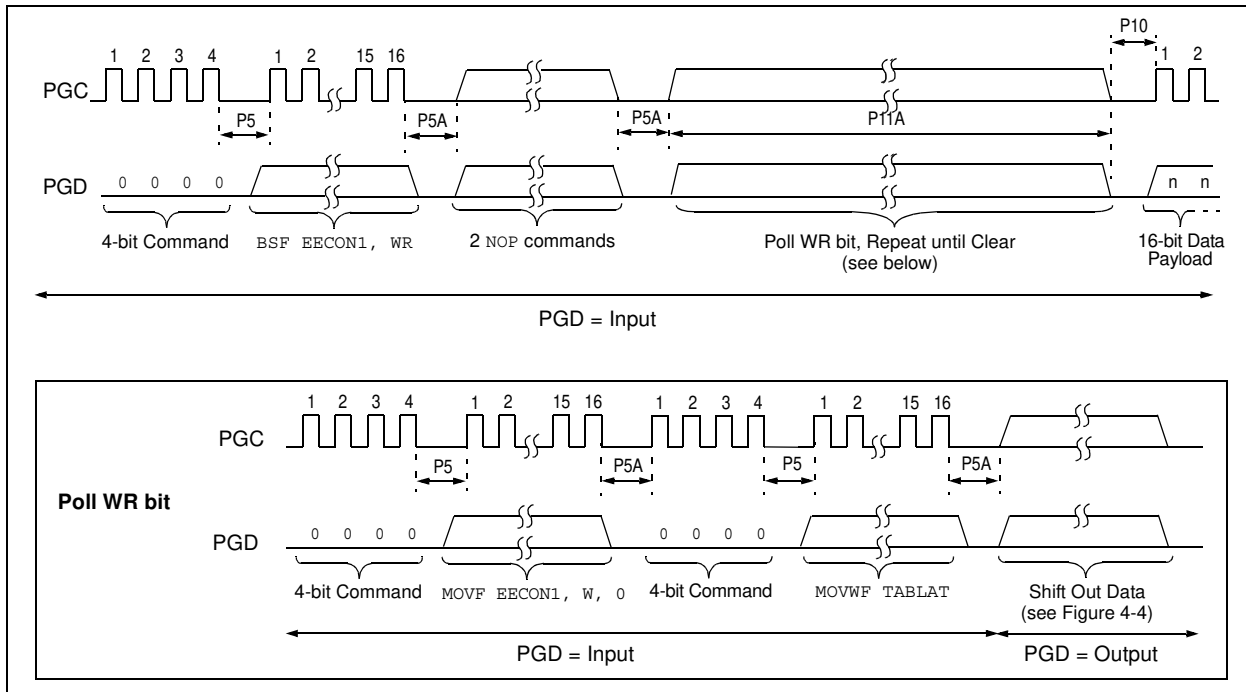


TABLE 3-7: PROGRAMMING DATA MEMORY

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to data EEPROM.		
0000	9E A6	BCF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 2: Set the data EEPROM Address Pointer.		
0000	0E <Addr>	MOVLW <Addr>
0000	6E A9	MOVWF EEADR
0000	0E <AddrH>	MOVLW <AddrH>
0000	6E AA	MOVWF EEADRH
Step 3: Load the data to be written.		
0000	0E <Data>	MOVLW <Data>
0000	6E A8	MOVWF EEDATA
Step 4: Enable memory writes.		
0000	84 A6	BSF EECON1, WREN
Step 5: Initiate write.		
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP
0000	00 00	NOP ;write starts on 4th clock of this instruction
Step 6: Poll WR bit, repeat until the bit is clear.		
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0010	<MSB><LSB>	Shift out data ⁽¹⁾
Step 7: Hold PGC low for time P10.		
Step 8: Disable writes.		
0000	94 A6	BCF EECON1, WREN
Repeat steps 2 through 8 to write more data.		

Note 1: See Figure 4-4 for details on shift out data timing.

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3.4 ID Location Programming

The ID locations are programmed much like the code memory. The ID registers are mapped in addresses 200000h through 200007h. These locations read out normally even after code protection.

Note: The user only needs to fill the first 8 bytes of the write buffer in order to write the ID locations.

Table 3-8 demonstrates the code sequence required to write the ID locations.

In order to modify the ID locations, refer to the methodology described in **Section 3.2.1 “Modifying Code Memory”**. As with code memory, the ID locations must be erased before being modified.

When VDD is below the minimum for Bulk Erase operation, ID locations can be cleared with the Row Erase method described in **Section 3.1.3 “ICSP Row Erase”**.

TABLE 3-8: WRITE ID SEQUENCE

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2: Set Table Pointer to ID. Load write buffer with 8 bytes and write.		
0000	0E 20	MOVLW 20h
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPTRH
0000	0E 00	MOVLW 00h
0000	6E F6	MOVWF TBLPTRL
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
1111	<MSB><LSB>	Write 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.

3.5 Boot Block Programming

The code sequence detailed in Table 3-5 should be used, except that the address used in “Step 2” will be in the range of 000000h to 0007FFh.

3.6 Configuration Bits Programming

Unlike code memory, the Configuration bits are programmed a byte at a time. The Table Write, Begin Programming 4-bit command ('1111') is used, but only 8 bits of the following 16-bit payload will be written. The LSB of the payload will be written to even addresses and the MSB will be written to odd addresses. The code sequence to program two consecutive configuration locations is shown in Table 3-9. See Figure 3-5 for the timing diagram.

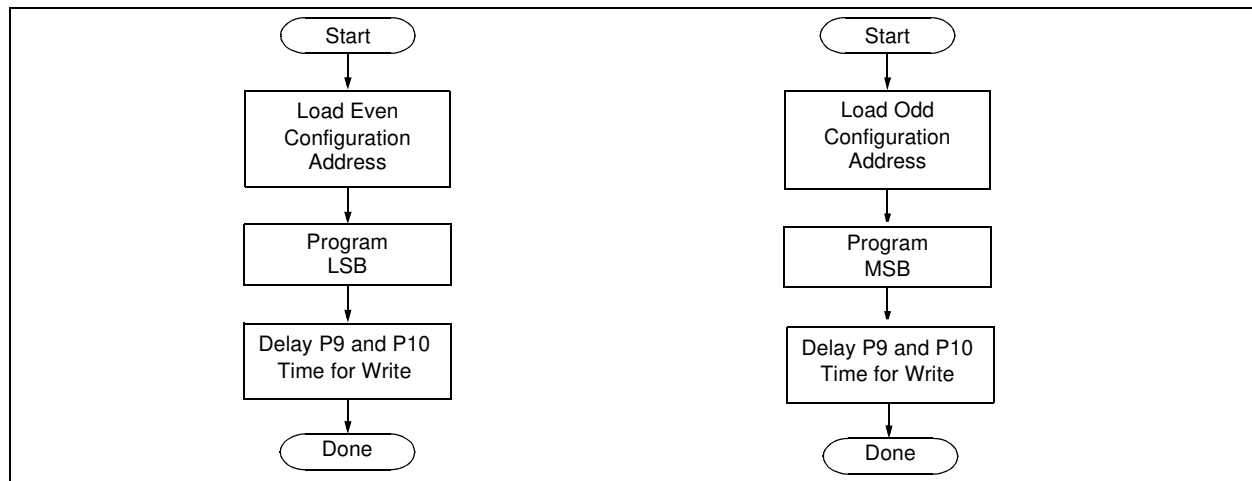
Note: The address must be explicitly written for each byte programmed. The addresses can not be incremented in this mode.

TABLE 3-9: SET ADDRESS POINTER TO CONFIGURATION LOCATION

4-bit Command	Data Payload	Core Instruction
Step 1: Direct access to config memory.		
0000	8E A6	BSF EECON1, EEPGD
0000	8C A6	BSF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2 ⁽¹⁾ : Set Table Pointer for config byte to be written. Write even/odd addresses.		
0000	0E 30	MOVLW 30h
0000	6E F8	MOVWF TBLPTRU
0000	0E 00	MOVLW 00h
0000	6E F7	MOVWF TBLPRTH
0000	0E 00	MOVLW 00h
0000	6E F6	MOVWF TBLPTRL
1111	<MSB ignored><LSB>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
0000	0E 01	MOVLW 01h
0000	6E F6	MOVWF TBLPTRL
1111	<MSB><LSB ignored>	Load 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9A and low for time P10.

Note 1: Enabling the write protection of Configuration bits (WRTC = 0 in CONFIG6H) will prevent further writing of Configuration bits. Always write all the Configuration bits before enabling the write protection for Configuration bits.

FIGURE 3-8: CONFIGURATION PROGRAMMING FLOW



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4.0 READING THE DEVICE

4.1 Read Code Memory, ID Locations and Configuration Bits

Code memory is accessed one byte at a time via the 4-bit command, '1001' (table read, post-increment). The contents of memory pointed to by the Table Pointer (TBLPTRU:TBLPTRH:TBLPTRL) are serially output on PGD.

The 4-bit command is shifted in LSb first. The read is executed during the next 8 clocks, then shifted out on PGD during the last 8 clocks, LSb to MSb. A delay of P6 must be introduced after the falling edge of the 8th

PGC of the operand to allow PGD to transition from an input to an output. During this time, PGC must be held low (see Figure 4-1). This operation also increments the Table Pointer by one, pointing to the next byte in code memory for the next read.

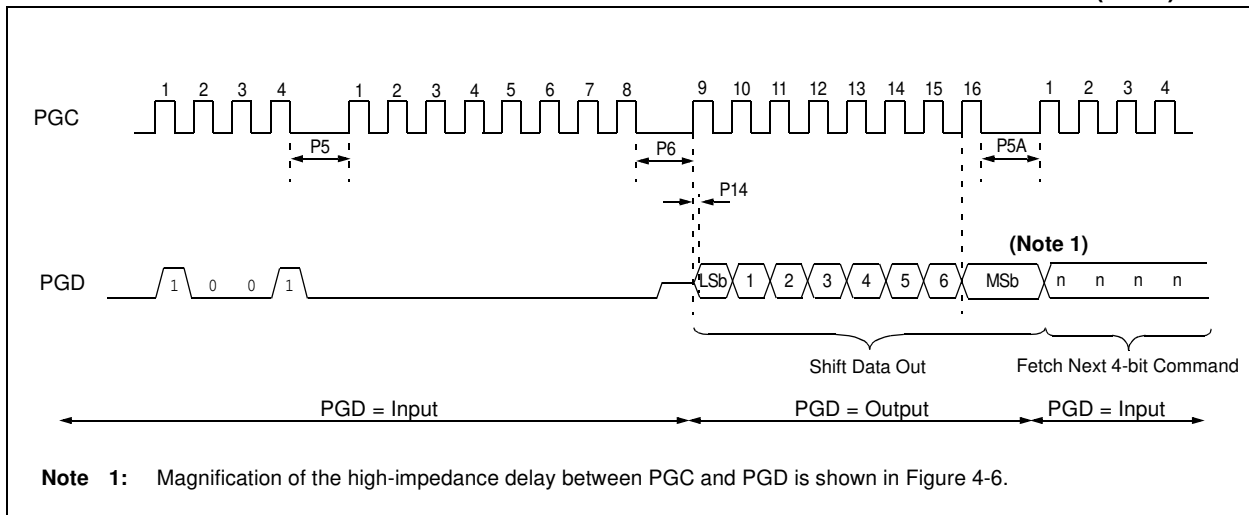
This technique will work to read any memory in the 000000h to 3FFFFFFh address space, so it also applies to the reading of the ID and Configuration registers.

Note: When table read protection is enabled, the first read access to a protected block should be discarded and the read repeated to retrieve valid data. Subsequent reads of the same block can be performed normally.

TABLE 4-1: READ CODE MEMORY SEQUENCE

4-bit Command	Data Payload	Core Instruction
Step 1: Set Table Pointer		
0000	0E <Addr[21:16]>	MOVLW Addr [21:16]
0000	6E F8	MOVWF TBLPTRU
0000	0E <Addr[15:8]>	MOVLW <Addr [15:8]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <Addr[7:0]>	MOVLW <Addr [7:0]>
0000	6E F6	MOVWF TBLPTRL
Step 2: Read memory and then shift out on PGD, LSb to MSb		
1001	00 00	TBLRD *+

FIGURE 4-1: TABLE READ POST-INCREMENT INSTRUCTION TIMING DIAGRAM (1001)



4.2 Verify Code Memory and ID Locations

The verify step involves reading back the code memory space and comparing it against the copy held in the programmer's buffer. Memory reads occur a single byte at a time, so two bytes must be read to compare against the word in the programmer's buffer. Refer to **Section 4.1 "Read Code Memory, ID Locations and Configuration Bits"** for implementation details of reading code memory.

The Table Pointer must be manually set to 200000h (base address of the ID locations) once the code memory has been verified. The post-increment feature of the table read 4-bit command can not be used to increment the Table Pointer beyond the code memory space. In a 64-Kbyte device, for example, a post-increment read of address FFFFh will wrap the Table Pointer back to 000000h, rather than point to unimplemented address 010000h.

FIGURE 4-2: VERIFY CODE MEMORY FLOW

